

SN54HC30, SN74HC30

8-Input Positive-NAND Gates

These devices contain a single 8-input NAND gate and perform the following Boolean functions in positive logic: $Y = \overline{A \cdot B \cdot C \cdot D \cdot E \cdot F \cdot G \cdot H}$ or $Y = \overline{A + B + C + D + E + F + G + H}$

The SN54HC30 is characterized for operation over the full military temperature range of -55°C to 125°C while the SN74HC30 is characterized for operation from -40°C to 85°C.

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
 - Class Q Military
 - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
 - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

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8-INPUT POSITIVE-NAND GATES

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D2884, DECEMBER 1982—REVISED SEPTEMBER 1987

- Package Options Include Plastic "Small Outline" Packages, Ceramic Chip Carriers, and Standard Plastic and Ceramic 300-mil DIPs
- Dependable Texas Instruments Quality and Reliability

description

These devices contain a single 8-input NAND gate and perform the following Boolean functions in positive logic:

$$Y = A \cdot B \cdot C \cdot D \cdot E \cdot F \cdot G \cdot H$$

or

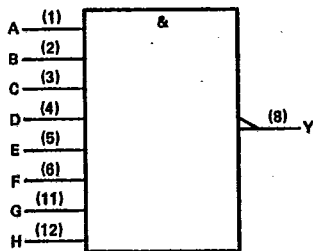
$$Y = \overline{A + B + C + D + E + F + G + H}$$

The SN54HC30 is characterized for operation over the full military temperature range of -55°C to 125°C. The SN74HC30 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE

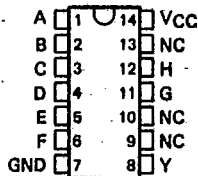
INPUTS A THRU H	OUTPUT Y
All Inputs H	L
One or more Inputs L	H

logic symbol†

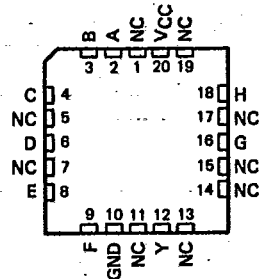


†This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for D, J, and N packages.

SN54HC30 . . . J PACKAGE
SN74HC30 . . . D OR N PACKAGE
(TOP VIEW)

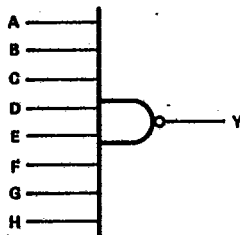


SN54HC30 . . . FK PACKAGE
(TOP VIEW)



NC—No internal connection

logic diagram (positive logic)



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HC MOS Devices

NOTICE

SEE ORDER OF DATA FOR ERRATA INFORMATION

PRODUCTION DATA documents contain information current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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8-INPUT POSITIVE-NAND GATES

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absolute maximum ratings over operating free-air temperature range†

Supply voltage, VCC	-0.5 V to 7 V
Input clamp current, I _{IK} (V _I < 0 or V _I > VCC)	±20 mA
Output clamp current, I _{OK} (V _O < 0 or V _O > VCC)	±20 mA
Continuous output current, I _O (V _O = 0 to VCC)	±25 mA
Continuous current through VCC or GND pins	±50 mA
Lead temperature 1,6 mm (1/16 in) from case for 60 s: FK or J package	300°C
Lead temperature 1,6 mm (1/16 in) from case for 10 s: D or N package	260°C
Storage temperature range	-65°C to 150°C

†Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

recommended operating conditions

		SN54HC30			SN74HC30			UNIT
		MIN	NOM	MAX	MIN	NOM	MAX	
V _{CC}	Supply voltage	2	5	6	2	5	6	V
V _{IH}	High-level input voltage	V _{CC} = 2 V	1.5		1.5			V
		V _{CC} = 4.5 V	3.15		3.15			
		V _{CC} = 6 V	4.2		4.2			
V _{IL}	Low-level input voltage	V _{CC} = 2 V	0	0.3	0	0.3		V
		V _{CC} = 4.5 V	0	0.9	0	0.9		
		V _{CC} = 6 V	0	1.2	0	1.2		
V _I	Input voltage	0		V _{CC}	0		V _{CC}	V
V _O	Output voltage	0		V _{CC}	0		V _{CC}	V
t _t	Input transition (rise and fall) times	V _{CC} = 2 V	0	1000	0	1000		ns
		V _{CC} = 4.5 V	0	500	0	500		
		V _{CC} = 6 V	0	400	0	400		
T _A	Operating free-air temperature	-65		125	-40		85	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{CC}	T _A = 25°C			SN54HC30		SN74HC30		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V _{OH}	V _I = V _{IH} or V _{IL} , I _{OH} = -20 μA	2 V	1.9	1.998		1.9	1.9		V	
		4.5 V	4.4	4.499		4.4	4.4			
		6 V	5.9	5.999		5.9	5.9			
	V _I = V _{IH} or V _{IL} , I _{OH} = -4 mA	4.5 V	3.98	4.30		3.7	3.84			
		6 V	5.48	5.80		5.2	5.34			
V _{OL}	V _I = V _{IH} or V _{IL} , I _{OL} = 20 μA	2 V	0.002	0.1		0.1	0.1		V	
		4.5 V	0.001	0.1		0.1	0.1			
		6 V	0.001	0.1		0.1	0.1			
	V _I = V _{IH} or V _{IL} , I _{OL} = 4 mA	4.5 V	0.17	0.26		0.4	0.33			
		6 V	0.15	0.26		0.4	0.33			
I _I	V _I = V _{CC} or 0	6 V	±0.1	±100		±1000	±1000	nA		
		I _{CC}	V _I = V _{CC} or 0, I _O = 0	6 V		2	40	20	μA	
C _i		2 to 6 V		3	10	10	10	pF		

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switching characteristics over recommended operating free-air temperature range (unless otherwise noted), $C_L = 50$ pF (see Note 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC}	T _A = 25 °C			SN54HC30		SN74HC30		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A thru H	Y	2 V	51	130	195	165	ns			
			4.5 V	15	26	39	33				
			6 V	12	22	33	28				
t _t		Y	2 V	28	75	110	95	ns			
			4.5 V	8	15	22	19				
			6 V	6	13	19	16				

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HC MOS Devices

C _{pd}	Power dissipation capacitance per gate	No load, T _A = 25 °C	22 pF typ
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NOTE 1: Load circuit and voltage waveforms are shown in Section 1.